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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151c6t6

List of figures

Table 5. Working mode-dependent functionalities (from Run/active down to standby)

Ips	Run/Active	Sleep	Low-power Run	Low-power Sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
CPU	Y	-	Y	-	-	-	-	-
Flash	Y	Y	Y	Y	-	-	-	-
RAM	Y	Y	Y	Y	Y	-	-	-
Backup Registers	Y	Y	Y	Y	Y	-	Y	-
EEPROM	Y	-	Y	Y	Y	-	-	-
Brown-out rest (BOR)	Y	Y	Y	Y	Y	Y	Y	-
DMA	Y	Y	Y	Y	-	-	-	-
Programmable Voltage Detector (PVD)	Y	Y	Y	Y	Y	Y	Y	-
Power On Reset (POR)	Y	Y	Y	Y	Y	Y	Y	-
Power Down Rest (PDR)	Y	Y	Y	Y	Y	-	Y	-
High Speed Internal (HSI)	Y	Y	-	-	-	-	-	-
High Speed External (HSE)	Y	Y	-	-	-	-	-	-
Low Speed Internal (LSI)	Y	Y	Y	Y	Y	-	Y	-
Low Speed External (LSE)	Y	Y	Y	Y	Y	-	Y	-
Multi-Speed Internal (MSI)	Y	Y	Y	Y	-	-	-	-
Inter-Connect Controller	Y	Y	Y	Y	-	-	-	-
RTC	Y	Y	Y	Y	Y	Y	Y	-
RTC Tamper	Y	Y	Y	Y	Y	Y	Y	Y
Auto Wakeup (AWU)	Y	Y	Y	Y	Y	Y	Y	Y
LCD	Y	Y	Y	Y	Y	-	-	-
USB	Y	Y	-	-	-	Y	-	-
USART	Y	Y	Y	Y	Y	(1)	-	-
SPI	Y	Y	Y	Y	-	-	-	-
I2C	Y	Y	Y	Y	-	(1)	-	-
ADC	Y	Y	-	-	-	-	-	-

Table 8. STM32L151x6/8/B and STM32L152x6/8/B pin definitions

Pins					Pin name	Pin type[1]	I/O structure	Main function[2] (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
1	-	-	B2	-	PE2	I/O	FT	PE2	TRACECLK/LCD_SEG38/ TIM3_ETR	-
2	-	-	A1	-	PE3	I/O	FT	PE3	TRACED0/LCD_SEG39/ TIM3_CH1	-
3	-	-	B1	-	PE4	I/O	FT	PE4	TRACED1/TIM3_CH2	-
4	-	-	C2	-	PE5	I/O	FT	PE5	TRACED2/TIM9_CH1	-
5	-	-	D2	-	PE6-WKUP3	I/O	FT	PE6	TRACED3/TIM9_CH2	WKUP3
6	1	B2	E2	1	V_{LCD}[3]	S		V_{LCD}	-	-
7	2	A2	C1	2	PC13-WKUP2	I/O	FT	PC13	-	RTC_TAMP1/ RTC_TS/ RTC_OUT/ WKUP2
8	3	A1	D1	3	PC14-OSC32_IN[4]	I/O	TC	PC14	-	OSC32_IN
9	4	B1	E1	4	PC15-OSC32_OUT[4]	I/O	TC	PC15	-	OSC32_OUT
10	-	-	F2	-	V_{SS_5}	S	-	V_{SS_5}	-	-
11	-	-	G2	-	V_{DD_5}	S	-	V_{DD_5}	-	-
12	5	C1	F1	5	PH0-OSC_IN[5]	I/O	TC	PH0	-	OSC_IN
13	6	D1	G1	6	PH1-OSC_OUT	I/O	TC	PH1	-	OSC_OUT
14	7	E1	H2	7	NRST	I/O	RST	NRST	-	-
15	8	E3	H1	-	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ /COMP1_INP
16	9	E2	J2	-	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP
17	10	F2	J3	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
18	11	-[6]	K2	-	PC3	I/O	TC	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP

Table 8. STM32L151x6/8/B and STM32L152x6/8/B pin definitions (continued)

Pins					Pin name	Pin type[1]	I/O structure	Main function[2] (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
19	12	F1	J1	8	V_{SSA}	S	-	V_{SSA}	-	-
20	-	-	K1	-	V_{REF-}	S	-	V_{REF-}	-	-
21	-	G1 (6)	L1	-	V_{REF+}	S	-	V_{REF+}	-	-
22	13	H1	M1	9	V_{DDA}	S	-	V_{DDA}	-	-
23	14	G2	L2	10	PA0-WKUP1	I/O	FT	PA0	USART2_CTS/ TIM2_CH1_ETR	WKUP1/ ADC_IN0/ COMP1_INP
24	15	H2	M2	11	PA1	I/O	FT	PA1	USART2_RTS/ TIM2_CH2/LCD_SEG0	ADC_IN1/ COMP1_INP
25	16	F3	K3	12	PA2	I/O	FT	PA2	USART2_TX/TIM2_CH3/ TIM9_CH1/LCD_SEG1	ADC_IN2/ COMP1_INP
26	17	G3	L3	13	PA3	I/O	TC	PA3	USART2_RX/TIM2_CH4/ TIM9_CH2/LCD_SEG2	ADC_IN3/ COMP1_INP
27	18	C2	E3	-	V_{SS_4}	S	-	V_{SS_4}	-	-
28	19	D2	H3	-	V_{DD_4}	S	-	V_{DD_4}	-	-
29	20	H3	M3	14	PA4	I/O	TC	PA4	SPI1_NSS/USART2_CK	ADC_IN4/ DAC_OUT1/ COMP1_INP
30	21	F4	K4	15	PA5	I/O	TC	PA5	SPI1_SCK/ TIM2_CH1_ETR	ADC_IN5/ DAC_OUT2/ COMP1_INP
31	22	G4	L4	16	PA6	I/O	FT	PA6	SPI1_MISO/TIM3_CH1/ LCD_SEG3/TIM10_CH1	ADC_IN6 /COMP1_INP
32	23	H4	M4	17	PA7	I/O	FT	PA7	SPI1_MOSI//TIM3_CH2/ LCD_SEG4/TIM11_CH1	ADC_IN7/ COMP1_INP
33	24	H5	K5	-	PC4	I/O	FT	PC4	LCD_SEG22	ADC_IN14/ COMP1_INP
34	25	H6	L5	-	PC5	I/O	FT	PC5	LCD_SEG23	ADC_IN15/ COMP1_INP

Table 8. STM32L151x6/8/B and STM32L152x6/8/B pin definitions (continued)

Pins					Pin name	Pin type(1)	I/O structure	Main function(2) (after reset)	Pins functions	
LQFP100	LQFP64	TFBGA64	UFBGA100	LQFP48 or UFQFPN48					Alternate functions	Additional functions
71	45	B8	A12	33	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
72	46	A8	A11	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
73	-	-	C11	-	PH2	I/O	FT	PH2	-	-
74	47	D5	F11	35	V_{SS_2}	S	-	V_{SS_2}	-	-
75	48	E5	G11	36	V_{DD_2}	S	-	V_{DD_2}	-	-
76	49	A7	A10	37	PA14	I/O	FT	JTCK -SWCLK	JTCK-SWCLK	-
77	50	A6	A9	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/PA15/ SPI1_NSS/ LCD_SEG17	-
78	51	B7	B11	-	PC10	I/O	FT	PC10	USART3_TX/LCD_SEG28 /LCD_SEG40/LCD_COM4	-
79	52	B6	C10	-	PC11	I/O	FT	PC11	USART3_RX/LCD_SEG29 /LCD_SEG41/LCD_COM5	-
80	53	C5	B10	-	PC12	I/O	FT	PC12	USART3_CK/LCD_SEG30 /LCD_SEG42/LCD_COM6	-
81	-	-	C9	-	PD0	I/O	FT	PD0	SPI2_NSS/TIM9_CH1	-
82	-	-	B9	-	PD1	I/O	FT	PD1	SPI2_SCK	-
83	54	B5	C8	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG31/ LCD_SEG43/LCD_COM7	-
84	-	-	B8	-	PD3	I/O	FT	PD3	USART2_CTS/ SPI2_MISO	-
85	-	-	B7	-	PD4	I/O	FT	PD4	USART2_RTS/ SPI2_MOSI	-
86	-	-	A6	-	PD5	I/O	FT	PD5	USART2_TX	-
87	-	-	B6	-	PD6	I/O	FT	PD6	USART2_RX	-
88	-	-	A5	-	PD7	I/O	FT	PD7	USART2_CK/TIM9_CH2	-
89	55	A5	A8	39	PB3	I/O	FT	JTDO	TIM2_CH2/PB3/ SPI1_SCK/LCD_SEG7/ JTDO	COMP2_INM

Table 9. Alternate function input/output (continued)

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO11	AFIO12	AFIO13	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART1/2/3	N/A	N/A	LCD	N/A	N/A	RI	SYSTEM
PB5	-	-	TIM3_CH2	-	I2C1_ SMBA	SPI1_MOSI	-	-	-	-	[SEG9]	-	-	-	EVENTOUT
PB6	-	-	TIM4_CH1	-	I2C1_SCL	-	-	USART1_TX	-	-	-	-	-	-	EVENTOUT
PB7	-	-	TIM4_CH2	-	I2C1_SDA	-	-	USART1_RX	-	-	-	-	-	-	EVENTOUT
PB8	-	-	TIM4_CH3	TIM10_CH1*	I2C1_SCL	-	-	-	-	-	SEG16	-	-	-	EVENTOUT
PB9	-	-	TIM4_CH4	TIM11_CH1*	I2C1_SDA	-	-	-	-	-	[COM3]	-	-	-	EVENTOUT
PB10	-	TIM2_CH3	-	-	I2C2_SCL	-	-	USART3_TX	-	-	SEG10	-	-	-	EVENTOUT
PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	SEG11	-	-	-	EVENTOUT
PB12	-	-	-	TIM10_CH1	I2C2_ SMBA	SPI2_NSS	-	USART3_CK	-	-	SEG12	-	-	-	EVENTOUT
PB13	-	-	-	TIM9_CH1	-	SPI2_SCK	-	USART3_CTS	-	-	SEG13	-	-	-	EVENTOUT
PB14	-	-	-	TIM9_CH2	-	SPI2_MISO	-	USART3_RTS	-	-	SEG14	-	-	-	EVENTOUT
PB15	-	-	-	TIM11_CH1	-	SPI2_MOSI	-	-	-	-	SEG15	-	-	-	EVENTOUT
PC0	-	-	-	-	-	-	-	-	-	-	SEG18	-	-	TIMx_IC1	EVENTOUT
PC1	-	-	-	-	-	-	-	-	-	-	SEG19	-	-	TIMx_IC2	EVENTOUT
PC2	-	-	-	-	-	-	-	-	-	-	SEG20	-	-	TIMx_IC3	EVENTOUT
PC3	-	-	-	-	-	-	-	-	-	-	SEG21	-	-	TIMx_IC4	EVENTOUT
PC4	-	-	-	-	-	-	-	-	-	-	SEG22	-	-	TIMx_IC1	EVENTOUT
PC5	-	-	-	-	-	-	-	-	-	-	SEG23	-	-	TIMx_IC2	EVENTOUT
PC6	-	-	TIM3_CH1	-	-	-	-	-	-	-	SEG24	-	-	TIMx_IC3	EVENTOUT
PC7	-	-	TIM3_CH2	-	-	-	-	-	-	-	SEG25	-	-	TIMx_IC4	EVENTOUT
PC8	-	-	TIM3_CH3	-	-	-	-	-	-	-	SEG26	-	-	TIMx_IC1	EVENTOUT
PC9	-	-	TIM3_CH4	-	-	-	-	-	-	-	SEG27	-	-	TIMx_IC2	EVENTOUT
PC10	-	-	-	-	-	-	-	USART3_TX	-	-	COM4 / SEG28 / SEG40	-	-	TIMx_IC3	EVENTOUT

Table 14. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	V
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.
2. Valid for device version without BOR at power up. Please see option "T" in Ordering information scheme for more details.

Table 19. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)			Unit
						55 °C	85 °C	105 °C	
I_{DD} (Sleep)	Supply current in Sleep mode, code executed from RAM, Flash switched OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	80	140	140	140	µA
				2 MHz	150	210	210	210	
				4 MHz	280	330	330	330(3)	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	280	400	400	400	
				8 MHz	450	550	550	550	
				16 MHz	900	1050	1050	1050	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	550	650	650	650	
				16 MHz	1050	1200	1200	1200	
				32 MHz	2300	2500	2500	2500	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	1100	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	2500	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	30	50	50	60	
		MSI clock, 524 kHz		524 kHz	50	70	70	80	
		MSI clock, 4.2 MHz		4.2 MHz	200	240	240	250	
	Supply current in Sleep mode, code executed from Flash	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	80	140	140	140	µA
				2 MHz	150	210	210	210	
				4 MHz	290	350	350	350	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	300	400	400	400	
				8 MHz	500	600	600	600	
				16 MHz	1000	1100	1100	1100	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	550	650	650	650	
				16 MHz	1050	1200	1200	1200	
				32 MHz	2300	2500	2500	2500	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	1000	1100	1100	1100	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	2300	2500	2500	2500	

Table 51. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)	-	3.0	3.6	V
V_{DI}(3)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(3)	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V_{OL}(4)	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}(4)	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. Guaranteed by characterization results.
4. Tested in production.
5. R_L is the load connected on the USB drivers.

Figure 25. USB timings: definition of data signal rise and fall time

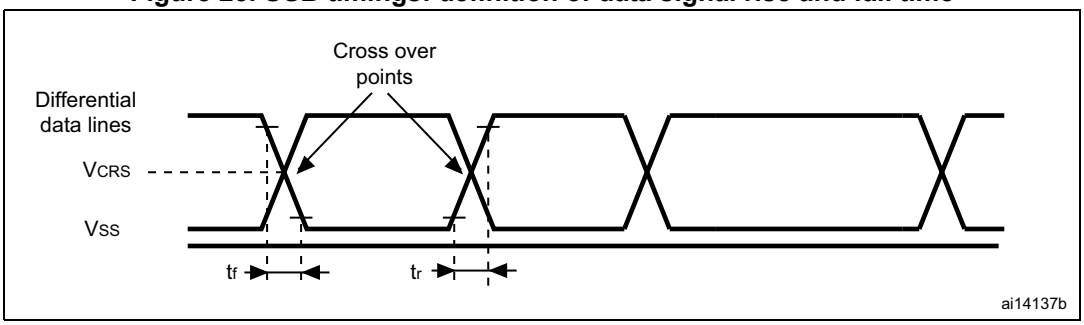


Table 52. USB: full speed electrical characteristics

Driver characteristics(1)					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall Time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage		1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

Table 55. ADC accuracy(1)(2)

Symbol	Parameter	Test conditions	Min(3)	Typ	Max(3)	Unit
ET	Total unadjusted error	$2.4\ V \le V_{DDA} \le 3.6\ V$ $2.4\ V \le V_{REF+} \le 3.6\ V$ $f_{ADC} = 8\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to $105\ °C$	-	2	4	LSB
EO	Offset error		-	1	2	
EG	Gain error		-	1.5	3.5	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1.7	3	
ENOB	Effective number of bits	$2.4\ V \le V_{DDA} \le 3.6\ V$ $V_{DDA} = V_{REF+}$ $f_{ADC} = 16\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to $105\ °C$ $1\ kHz \le F_{input} \le 100\ kHz$	9.2	10	-	bits
SINAD	Signal-to-noise and distortion ratio		57.5	62	-	dB
SNR	Signal-to-noise ratio		57.5	62	-	
THD	Total harmonic distortion		-74	-75	-	
ET	Total unadjusted error	$2.4\ V \le V_{DDA} \le 3.6\ V$ $1.8\ V \le V_{REF+} \le 2.4\ V$ $f_{ADC} = 4\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to $105\ °C$	-	4	6.5	LSB
EO	Offset error		-	2	4	
EG	Gain error		-	4	6	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1.5	3	
ET	Total unadjusted error	$1.8\ V \le V_{DDA} \le 2.4\ V$ $1.8\ V \le V_{REF+} \le 2.4\ V$ $f_{ADC} = 4\ MHz$, $R_{AIN} = 50\ \Omega$ $T_A = -40$ to $105\ °C$	-	2	3	LSB
EO	Offset error		-	1	1.5	
EG	Gain error		-	1.5	2	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	1	1.5	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.12* does not affect the ADC accuracy.
3. Guaranteed by characterization results.

Figure 26. ADC accuracy characteristics

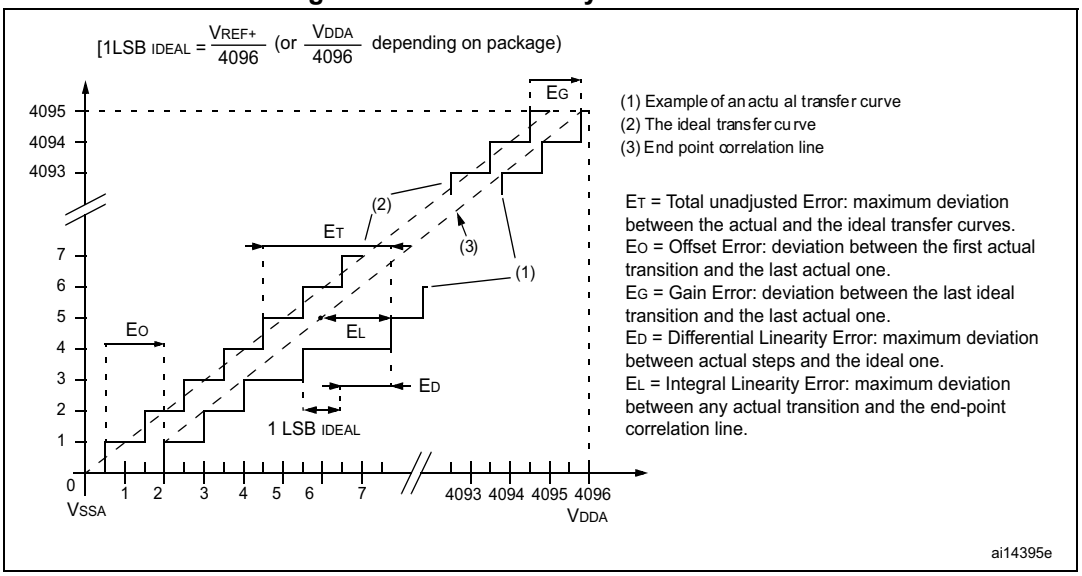
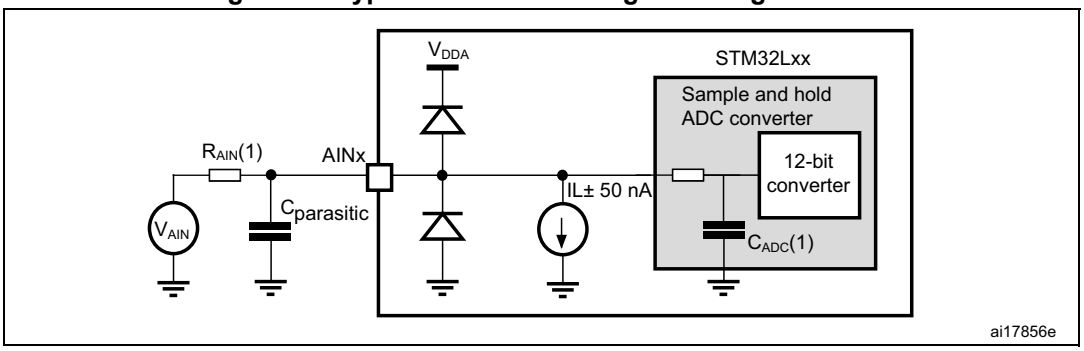
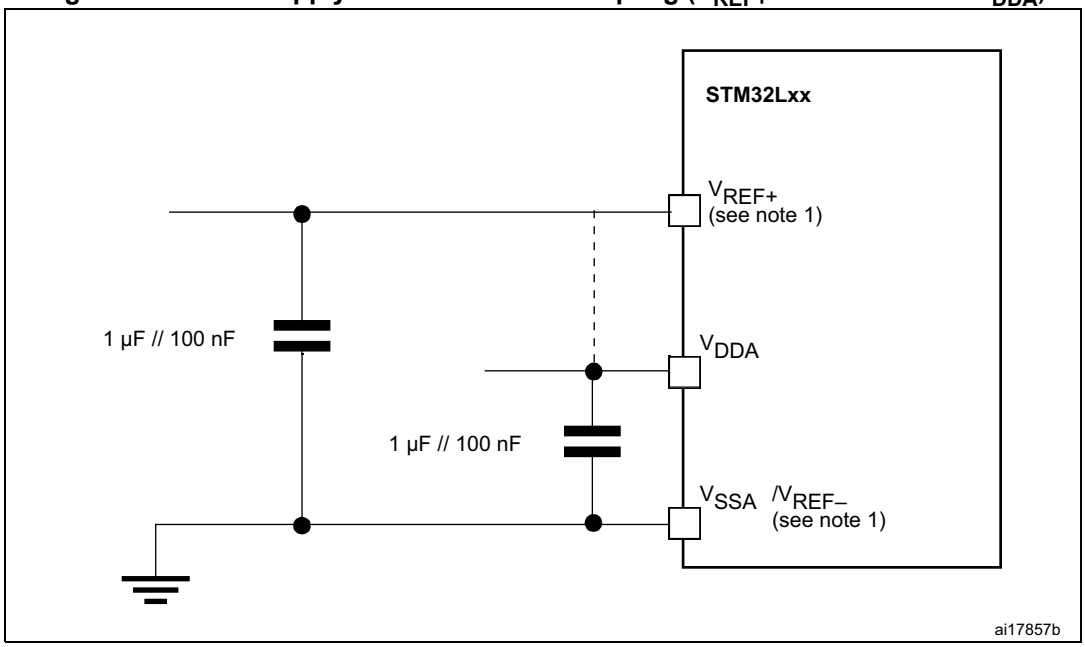


Figure 27. Typical connection diagram using the ADC



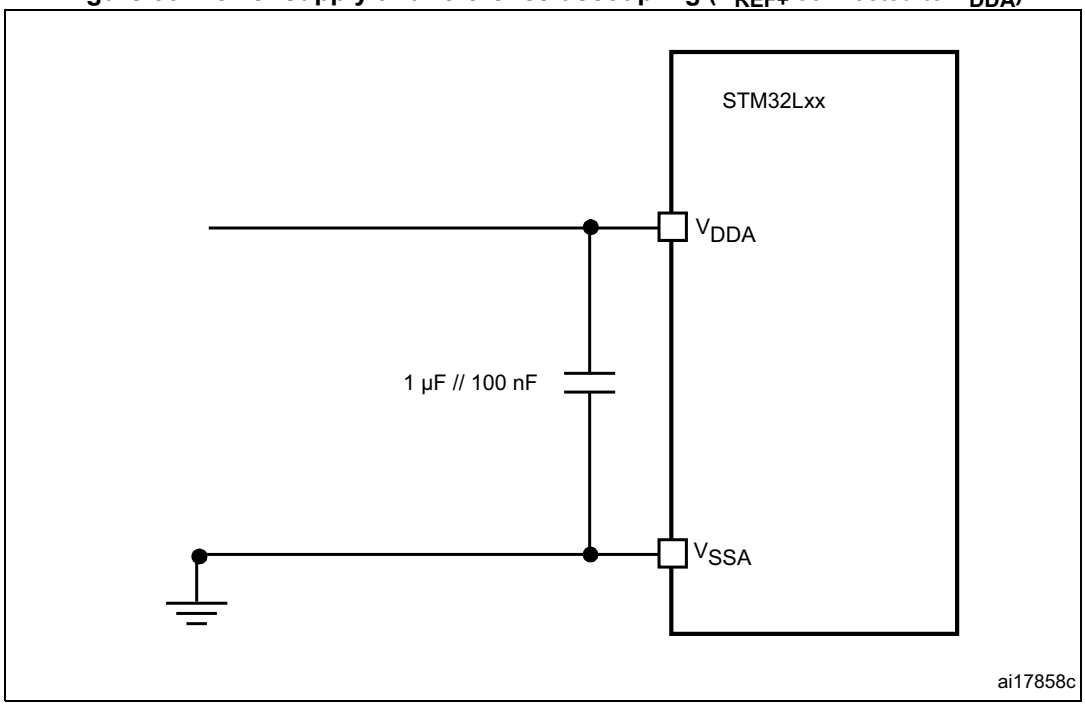
1. Refer to *Table 56: Maximum source impedance RAIN max* for the value of R_{AIN} and *Table 54: ADC characteristics* for the value of CADC
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

Figure 29. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



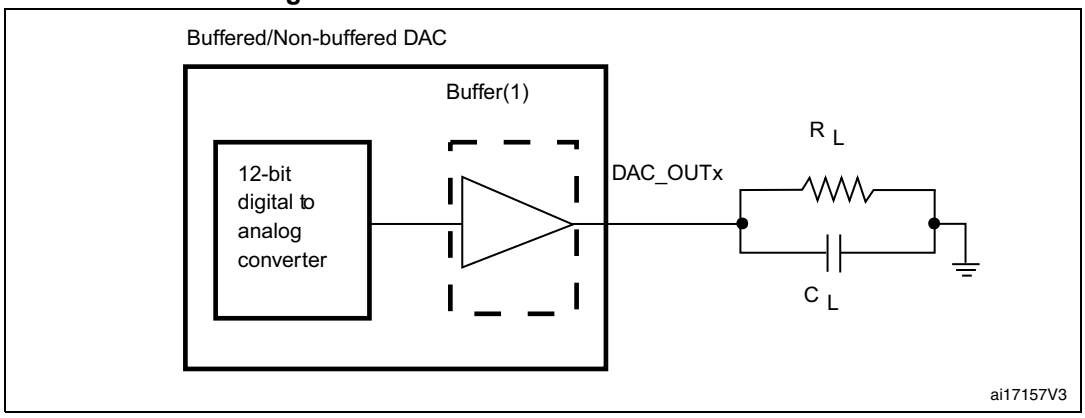
1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

Figure 30. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

Figure 31. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

6.3.19 Temperature sensor characteristics

Table 58. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3 V	0x1FF8 007A-0x1FF8 007B
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C V_{DDA}= 3 V	0x1FF8 007E-0x1FF8 007F

Table 59. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(4)(3)	ADC sampling time when reading the temperature	10	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.
4. Shortest sampling time can be determined in the application by multiple iterations.

6.3.21 LCD controller (STM32L152xx only)

The STM32L152xx embeds a built-in step-up converter to provide a constant LCD reference voltage independently from the V_{DD} voltage. An external capacitor C_{ext} must be connected to the V_{LCD} pin to decouple this converter.

Table 62. LCD controller characteristics

Symbol	Parameter	Min	Typ	Max	Unit
V_{LCD}	LCD external voltage	-	-	3.6	V
V_{LCD0}	LCD internal reference voltage 0	-	2.6	-	
V_{LCD1}	LCD internal reference voltage 1	-	2.73	-	
V_{LCD2}	LCD internal reference voltage 2	-	2.86	-	
V_{LCD3}	LCD internal reference voltage 3	-	2.98	-	
V_{LCD4}	LCD internal reference voltage 4	-	3.12	-	
V_{LCD5}	LCD internal reference voltage 5	-	3.26	-	
V_{LCD6}	LCD internal reference voltage 6	-	3.4	-	
V_{LCD7}	LCD internal reference voltage 7	-	3.55	-	
C_{ext}	V_{LCD} external capacitance	0.1	-	2	µF
I_{LCD}(1)	Supply current at V_{DD} = 2.2 V	-	3.3	-	µA
	Supply current at V_{DD} = 3.0 V	-	3.1	-	
R_{Htot}(2)	Low drive resistive network overall value	5.28	6.6	7.92	MΩ
R_L(2)	High drive resistive network total value	192	240	288	kΩ
V_{44}	Segment/Common highest level voltage	-	-	V_{LCD}	V
V_{34}	Segment/Common 3/4 level voltage	-	3/4 V_{LCD}	-	V
V_{23}	Segment/Common 2/3 level voltage	-	2/3 V_{LCD}	-	
V_{12}	Segment/Common 1/2 level voltage	-	1/2 V_{LCD}	-	
V_{13}	Segment/Common 1/3 level voltage	-	1/3 V_{LCD}	-	
V_{14}	Segment/Common 1/4 level voltage	-	1/4 V_{LCD}	-	
V_0	Segment/Common lowest level voltage	0	-	-	
ΔVxx(3)	Segment/Common level voltage error T_A = -40 to 85 °C	-	-	±50	mV

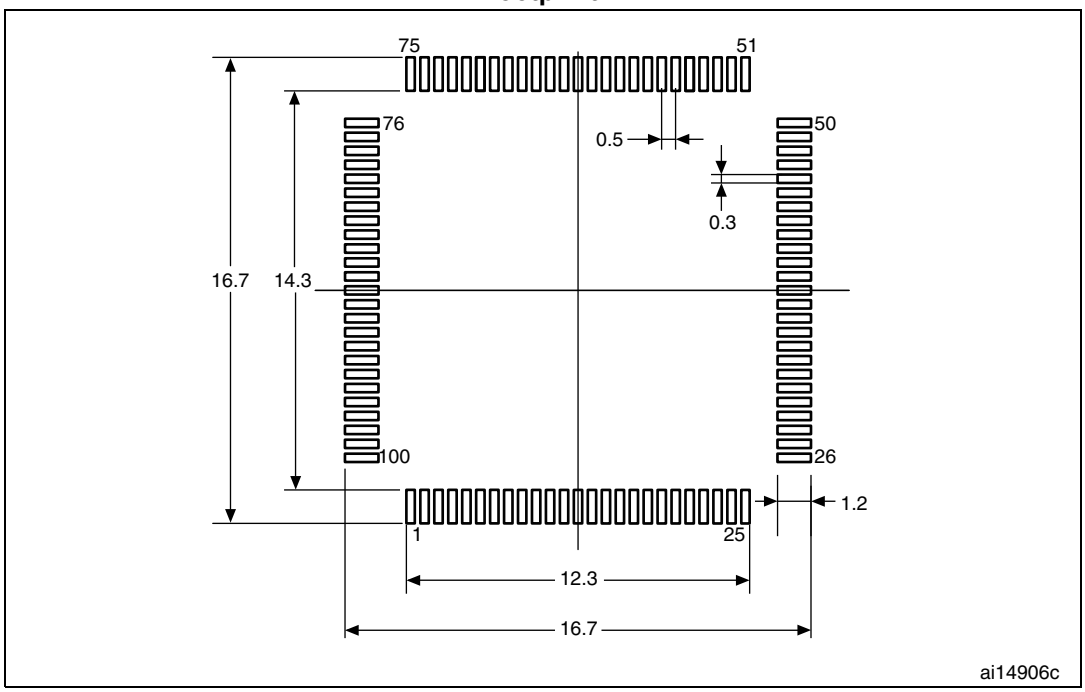
1. LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected
2. Guaranteed by design.
3. Guaranteed by characterization results.

Table 63. LQPF100 14 x 14 mm, 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 33. LQPF100 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint

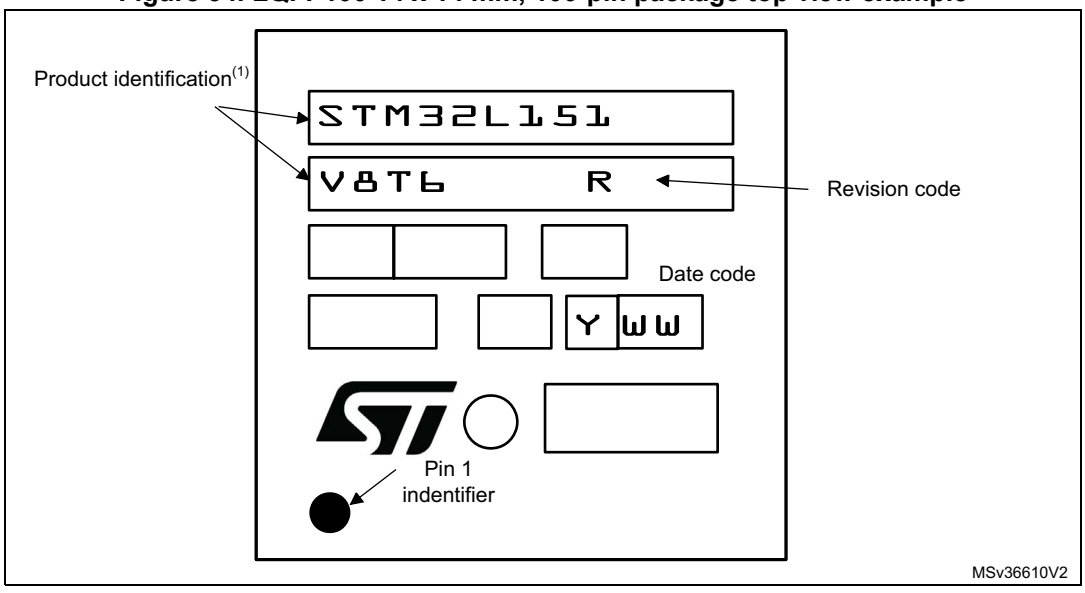


1. Dimensions are in millimeters.

LQFP100 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

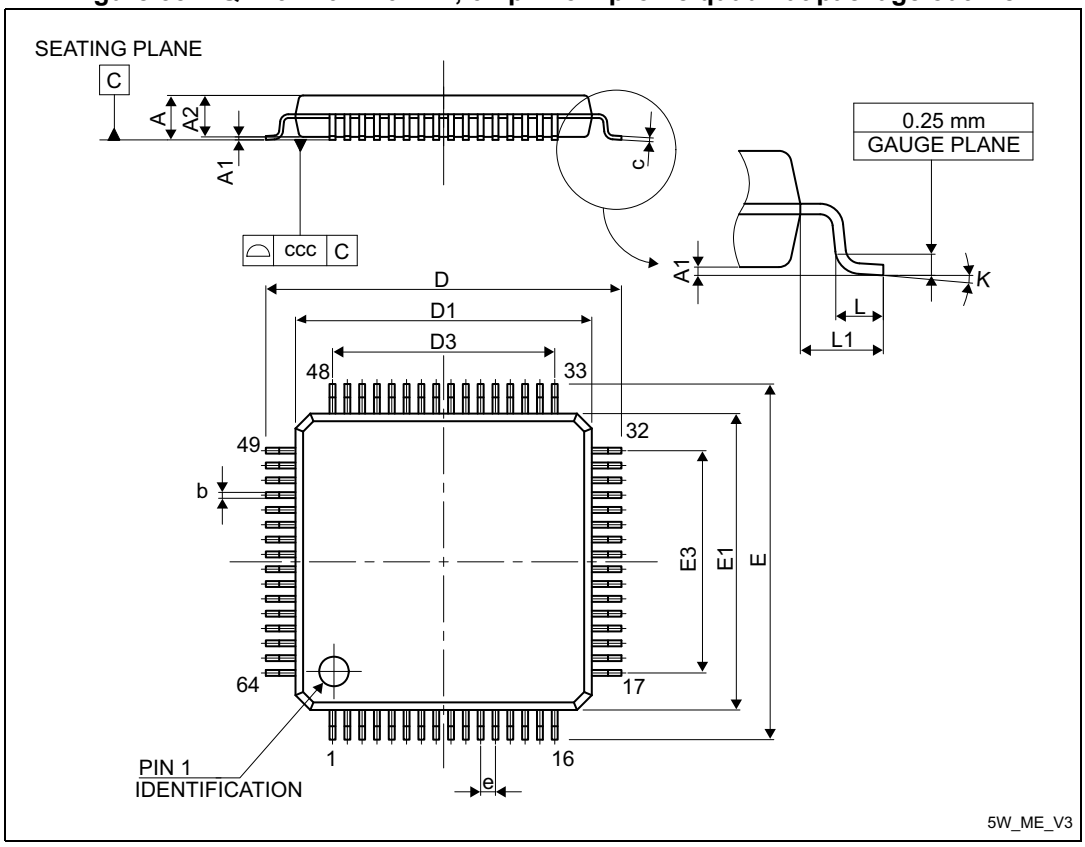
Figure 34. LQFP100 14 x 14 mm, 100-pin package top view example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.2 LQFP64 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 35. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package outline



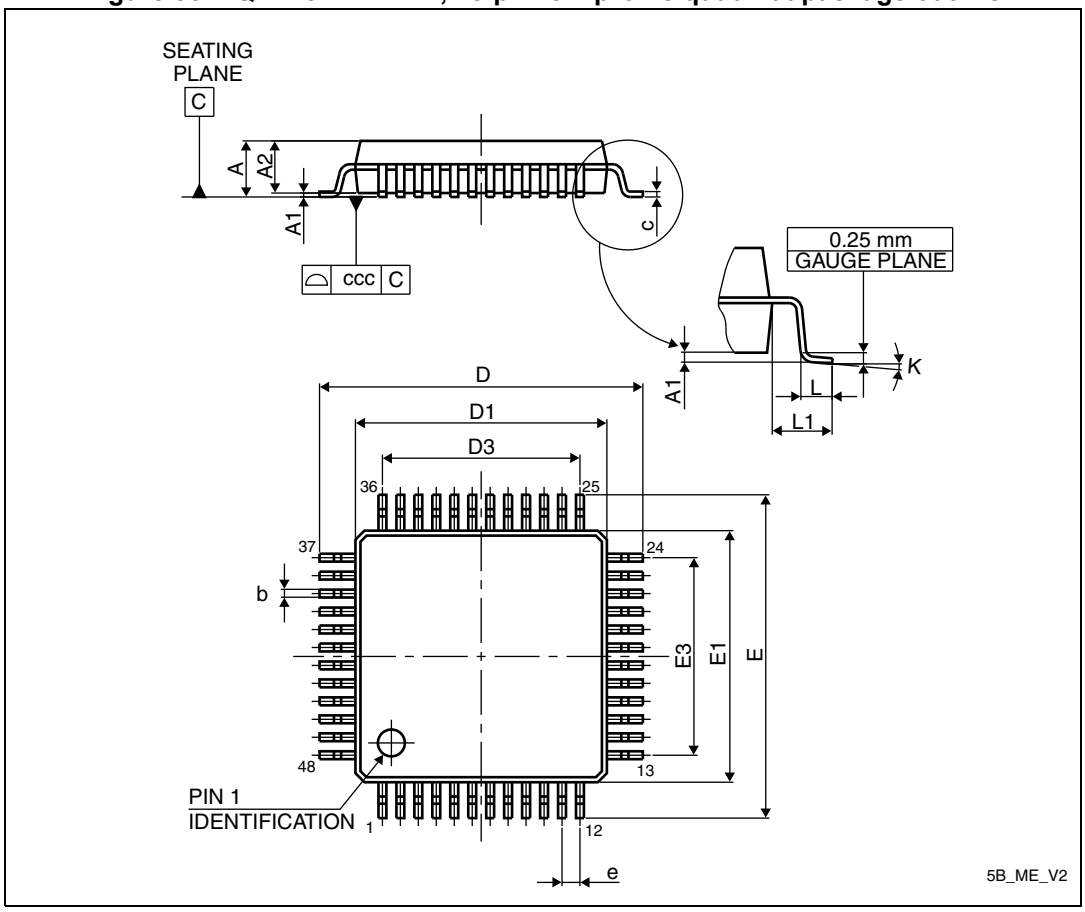
1. Drawing is not to scale.

Table 64. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Typ	Min	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

7.3 LQFP48 7 x 7 mm, 48-pin low-profile quad flat package information

Figure 38. LQFP48 7 x 7 mm, 48-pin low-profile quad flat package outline



1. Drawing is not to scale.

8 Ordering information

Table 72. Ordering information scheme

Example: STM32 L 151 C 8 T 6 T TR

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low power

Device subfamily

151: Devices without LCD

152: Devices with LCD

Pin count

C = 48 pins

R = 64 pins

V = 100 pins

Flash memory size

6 = 32 Kbytes of Flash memory

8 = 64 Kbytes of Flash memory

B = 128 Kbytes of Flash memory

Package

H = BGA

T = LQFP

U = UFQFPN

Temperature range

6 = Industrial temperature range, –40 to 85 °C

Options

No character = V_{DD} range: 1.8 to 3.6 V and BOR enabled

T = V_{DD} range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 73. Document revision history (continued)

Date	Revision	Changes
12-Nov-2013	9	Changed voltage Range 1 minimum to 1.71 V and updated dynamic voltage scaling range in *Table 3: Functionalities depending on the operating power supply range* Updated LCD and ADC features in *Table 2: Ultralow power STM32L15xx6/8/B device features and peripheral counts*. Updated *Table 3: Functionalities depending on the operating power supply range*. Updated *Table 5: Working mode-dependent functionalities (from Run/active down to standby)*. Updated *Figure 3: STM32L15xVx UFBGA100 ballout* Added *Table 7: Legend/abbreviations used in the pinout table*. Updated *Table 8: STM32L15xx6/8/B pin definitions* Updated *Figure 10: Pin loading conditions* and *Figure 11: Pin input voltage*. Updated *Figure 12: Power supply scheme*. Replaced “Σ” by “σ” in *Section 6.1.1* and *Section 6.1.2*. Updated *Table 10: Voltage characteristics*. Updated *Table 13: General operating conditions*. Added *Section 6.1.7: Optional LCD power supply scheme*. Updated *Table 16: Embedded internal reference voltage*. Added this *Note* in *Section : High-speed external clock generated from a crystal/ceramic resonator* Updated *Section : Functional susceptibility to I/O current injection*. This *Section 6.3.5: Wakeup time from Low power mode* was previously a paragraph in *Section 6.3.4: Supply current characteristics*. Updated f_{HSE} conditions in *Table 17: Current consumption in Run mode, code with data processing running from Flash* and *Table 18: Current consumption in Run mode, code with data processing running from RAM*. Fixed IDD unit in *Table 23: Typical and maximum current consumptions in Standby mode*. This *Figure 15: High-speed external clock source AC timing diagram* was moved up (was previously after *Figure 16: Low-speed external clock source AC timing diagram*. Updated first sentence in *Section 6.3.14: NRST pin characteristics*. Updated *Table 25: Low-power mode wakeup timings* title. Updated *Table 26: High-speed external user clock characteristics* Updated *Table 28: HSE oscillator characteristics* and *Table 29: LSE oscillator characteristics (fLSE = 32.768 kHz)*. Updated *Section 6.3.11: Electrical sensitivity characteristics* title. Updated *Table 39: ESD absolute maximum ratings*. Updated *Table 41: I/O current injection susceptibility* and *Table 42: I/O static characteristics*. Updated *Figure 21: I2C bus AC waveforms and measurement circuit*. Removed any occurrence of “when 8 pins are sourced at same time” in *Table 43: Output voltage characteristics*. Updated section link in second paragraph of *Section 6.3.15: TIM timer characteristics*.